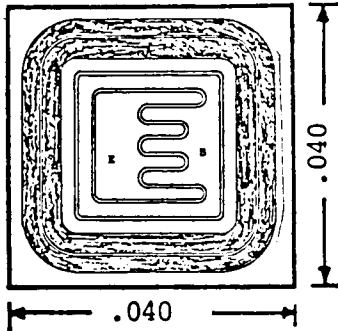


X00221

STX725 CHIP

HIGH VOLTAGE NPN TRANSISTOR CHIP

www.datasheet4u.com



Contact Area: .005 x .005

CONTACT METALLIZATION

Base/Emitter: > 30,000 Å Aluminum

Collector: > 2,000 Å Evaporated Gold

ASSEMBLY RECOMMENDATIONS

1. Eutectic Die Attach.
2. Ultrasonically Attach 2 MIL Aluminum Wire To Base/Emitter Contacts.

PARAMETER	TEST CONDITIONS	TYPE	MIN.	MAX.	UNIT
$BV_{CEO}$	$I_C = 1 \text{ mA}$ (pulsed)		450		Vdc
$BV_{CBO}$	$I_C = 100 \text{ uA}$		600		Vdc
$BV_{CER}$	$I_C = 100 \text{ uA}$ , $R_{BE} = 5 \text{ K Ohm}$		600		Vdc
$BV_{EBO}$	$I_E = 20 \text{ uA}$		6		Vdc
$I_{EBO}$	$V_{EB} = 4 \text{ V}$			250	n Adc
$I_{CBO}$	$V_{CB} = 500 \text{ V}$			500	n Adc
$h_{FE}$	$V_{CE} = 10 \text{ V}$ , $I_C = 1 \text{ mA}$		25	250	
$h_{FE}$	$V_{CE} = 5 \text{ V}$ , $I_C = 25 \text{ mA}$		50	300	
$h_{FE}$	$V_{CE} = 5 \text{ V}$ , $I_C = 100 \text{ mA}$		15	250	
$V_{BE(SAT)}$	$I_C = 25 \text{ mA}$ , $V_{CE} = 5 \text{ V}$			1.0	Vdc
$V_{CE(SAT)}$	$I_C = 25 \text{ mA}$ , $I_B = 2.5 \text{ mA}$			500	mVdc
$C_{OB}$	$V_{CB} = 15 \text{ V}$			15	pf
$f_T$	$V_{CE} = 10 \text{ V}$ , $I_C = 50 \text{ mA}$ $f = 20 \text{ MHz}$		25		MHz

Electrical characteristics measured at lot acceptance testing in a TO-5 package. Specifications subject to change without notice.

**SSDI** SOLID STATE DEVICES, INC.

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